FIG.1

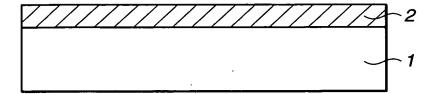


FIG.2

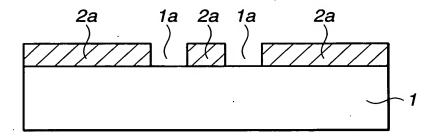


FIG.3

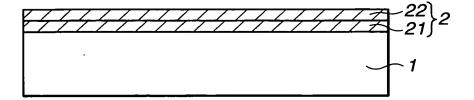


FIG.4

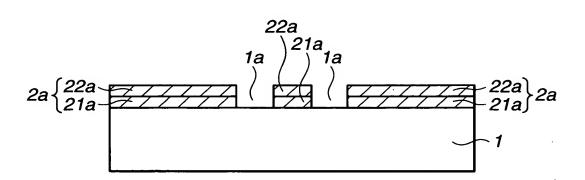


FIG.5

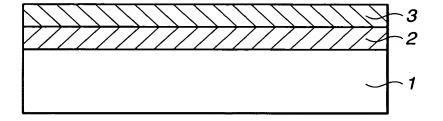


FIG.6

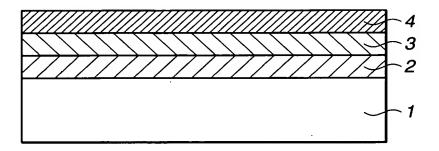
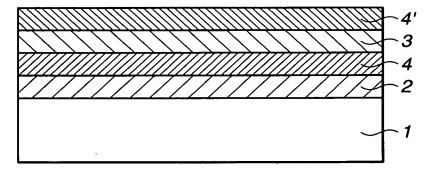


FIG.7



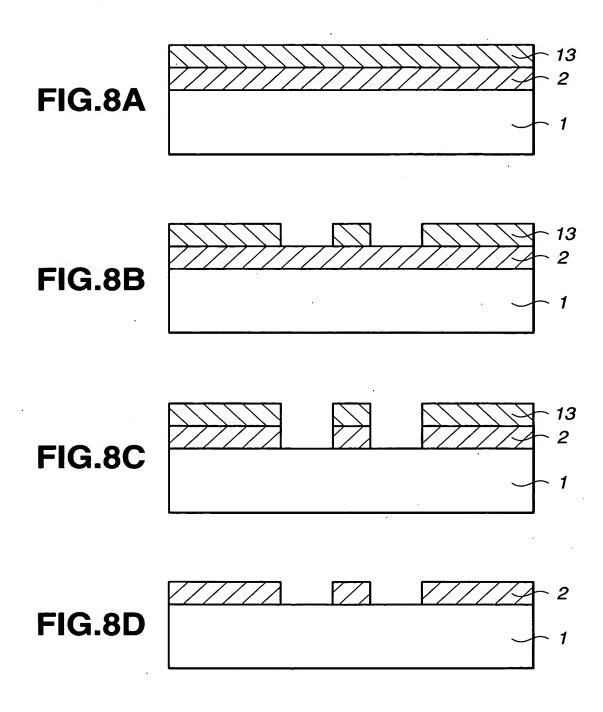


FIG.9

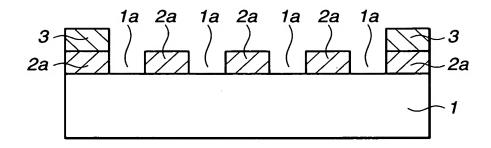


FIG.10A FIG.10B

ELECTRIC FIELD OF THROUGH MASK

LIGHT INTENSITY AT WAFER

FIG.11

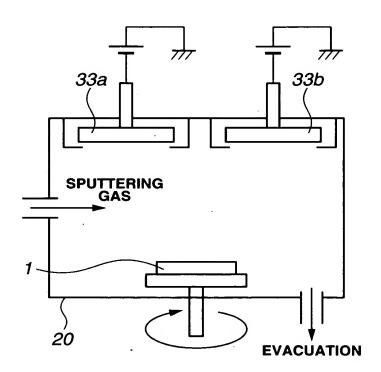


FIG.12

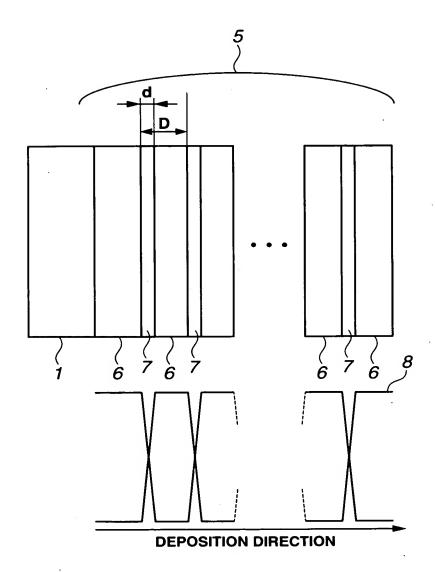


FIG.13

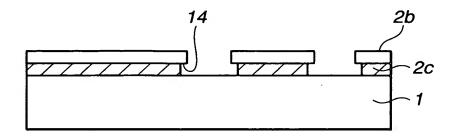


FIG.14

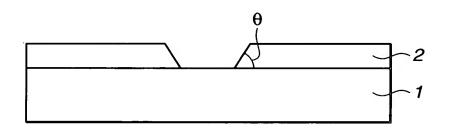


FIG.15

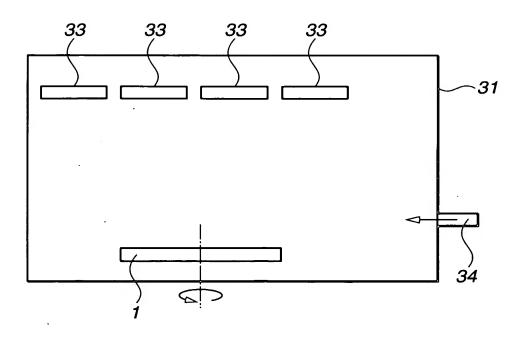
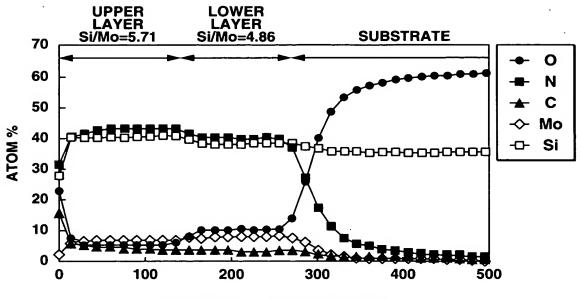


FIG.16

RESULTS OF DEPTHWISE ANALYSIS



ETCHING TIME (sec) [Ar0 (600V)]

FIG.17

RESULTS OF DEPTHWISE ANALYSIS

